20V P-Channel Enhancement Mode MOSFET

Description

The NP2301AVR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as

Electrical Characteristics (TA=25 unless otherwise noted)



Typical Performance Characteristics

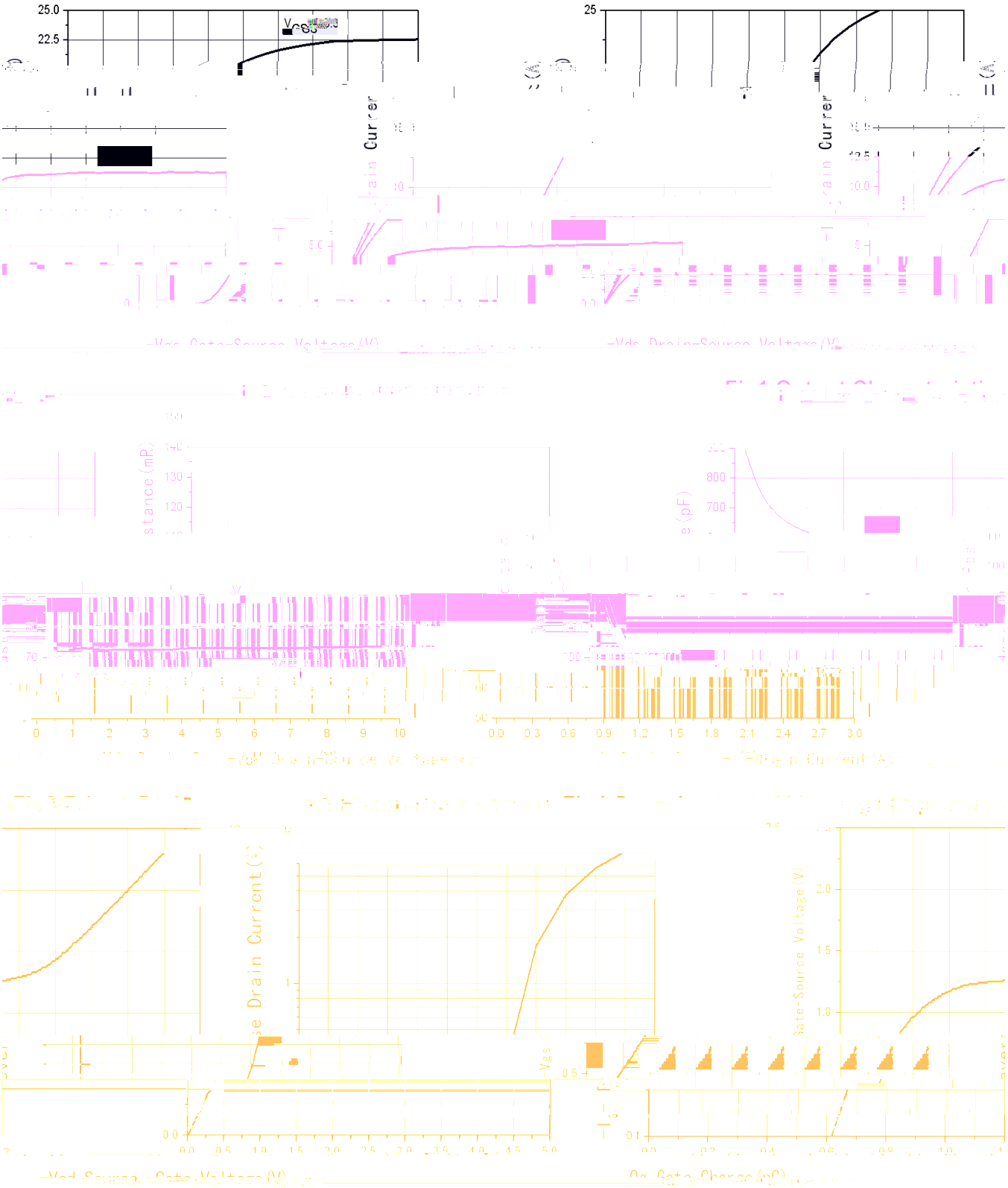
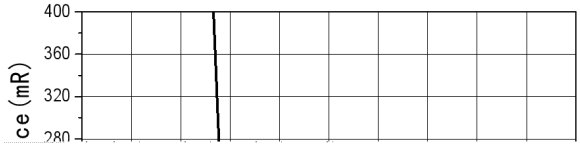
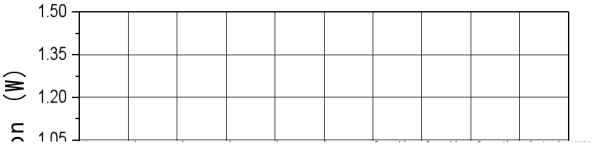


Fig5 Source-Drain Diode Forward　　Fig6 Gate Charge


400
360
320
280
ce (mR)


1.50
1.35
1.20
(W)

Package Information

SOT-23